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an insulating layer covering the plurality of gate stacks, the at least one component and the silicide, the insulating layer having a plurality of contact holes therein, the plurality of contact holes being formed by etching the insulating layer to provide the plurality of contact holes, the insulating layer etching step using the silicide as an etch stop layer to ensure that the insulating etching step does not etch through the polysilicon layer; and

a conductor for filling the plurality of contact holes;

wherein the silicide layer resides on the first polysilicon layer but not between the plurality of floating gates and the plurality of control gates in the plurality of gate stacks.
